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Inverting Regulator - Buck, Boost, Switching

1.5 A

MC34063A, MC33063A, SC33063A, NCV33063A

The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step–Down and Step–Up and Voltage–Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

Features

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

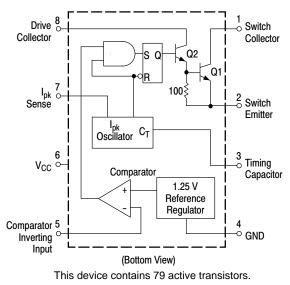
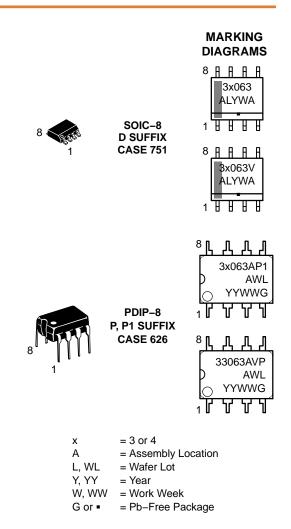


Figure 1. Representative Schematic Diagram



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

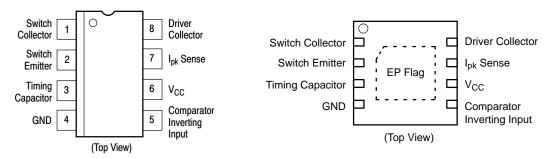


Figure 2. Pin Connections

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	V _{CC}	40	Vdc
Comparator Input Voltage Range	V _{IR}	-0.3 to +40	Vdc
Switch Collector Voltage	V _{C(switch)}	40	Vdc
Switch Emitter Voltage (V _{Pin 1} = 40 V)	V _{E(switch)}	40	Vdc
Switch Collector to Emitter Voltage	V _{CE(switch)}	40	Vdc
Driver Collector Voltage	V _{C(driver)}	40	Vdc
Driver Collector Current (Note 1)	I _{C(driver)}	100	mA
Switch Current	I _{SW}	1.5	А
Power Dissipation and Thermal Characteristics			
Plastic Package, P, P1 Suffix			
$T_A = 25^{\circ}C$	P _D	1.25	W
Thermal Resistance	R _{θJA}	115	°C/W
SOIC Package, D Suffix			
$T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance	R _{θJA}	160	°C/W
Thermal Resistance	R _{θJC}	45	°C/W
DFN Package			
$T_A = 25^{\circ}C$	PD	1.25	mW
Thermal Resistance	R _{θJA}	80	°C/W
Operating Junction Temperature	TJ	+150	°C
Operating Ambient Temperature Range	T _A		°C
MC34063A		0 to +70	
MC33063AV, NCV33063A		-40 to +125	
MC33063A, SC33063A		-40 to +85	
Storage Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Maximum package power dissipation limits must be observed.

2. This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL–STD–883, Method 3015. Machine Model Method 400 V.

3. NCV prefix is for automotive and other applications requiring site and change control.

ELECTRICAL CHARACTERISTICS	V _{CC} = 5.0 V, T _A = T _{low} to T _{high} [Note 4], unless otherwise specified.)
----------------------------	---	---

Characteristics	Symbol	Min	Тур	Max	Unit
OSCILLATOR					
Frequency (V _{Pin 5} = 0 V, C _T = 1.0 nF, T _A = 25°C)	f _{osc}	24	33	42	kHz
Charge Current (V _{CC} = 5.0 V to 40 V, $T_A = 25^{\circ}C$)	I _{chg}	24	35	42	μΑ
Discharge Current (V _{CC} = 5.0 V to 40 V, $T_A = 25^{\circ}C$)	I _{dischg}	140	220	260	μΑ
Discharge to Charge Current Ratio (Pin 7 to V_{CC} , $T_A = 25^{\circ}C$)	I _{dischg} /I _{chg}	5.2	6.5	7.5	_
Current Limit Sense Voltage ($I_{chg} = I_{dischg}$, $T_A = 25^{\circ}C$)	V _{ipk(sense)}	250	300	350	mV
OUTPUT SWITCH (Note 5)					
Saturation Voltage, Darlington Connection (I _{SW} = 1.0 A, Pins 1, 8 connected)	V _{CE(sat)}	-	1.0	1.3	V
Saturation Voltage (Note 6) (I _{SW} = 1.0 A, R _{Pin 8} = 82 Ω to V _{CC} , Forced $\beta \simeq 20$)	V _{CE(sat)}	-	0.45	0.7	V
DC Current Gain (I_SW = 1.0 A, V_{CE} = 5.0 V, T_A = 25^{\circ}C)	h _{FE}	50	75	-	_
Collector Off-State Current (V _{CE} = 40 V)	I _{C(off)}	-	0.01	100	μΑ
COMPARATOR					
Threshold Voltage $T_A = 25^{\circ}C$ $T_A = T_{low}$ to T_{high}	V _{th}	1.225 1.21	1.25 -	1.275 1.29	V
Threshold Voltage Line Regulation (V _{CC} = 3.0 V to 40 V) MC33063, MC34063 MC33063V, NCV33063	Reg _{line}		1.4 1.4	5.0 6.0	mV
Input Bias Current (V _{in} = 0 V)	I _{IB}	-	-20	-400	nA
TOTAL DEVICE		•	•	•	-
Supply Current (Vac = 5.0 V to 40 V C = 1.0 pE Pip 7 = Vac	laa		1	4.0	m۸

Supply Current (V _{CC} = 5.0 V to 40 V, C _T = 1.0 nF, Pin 7 = V _{CC} , V _{Pin 5} > V _{th} , Pin 2 = GND, remaining pins open)	I _{CC}	-	-	4.0	mA	
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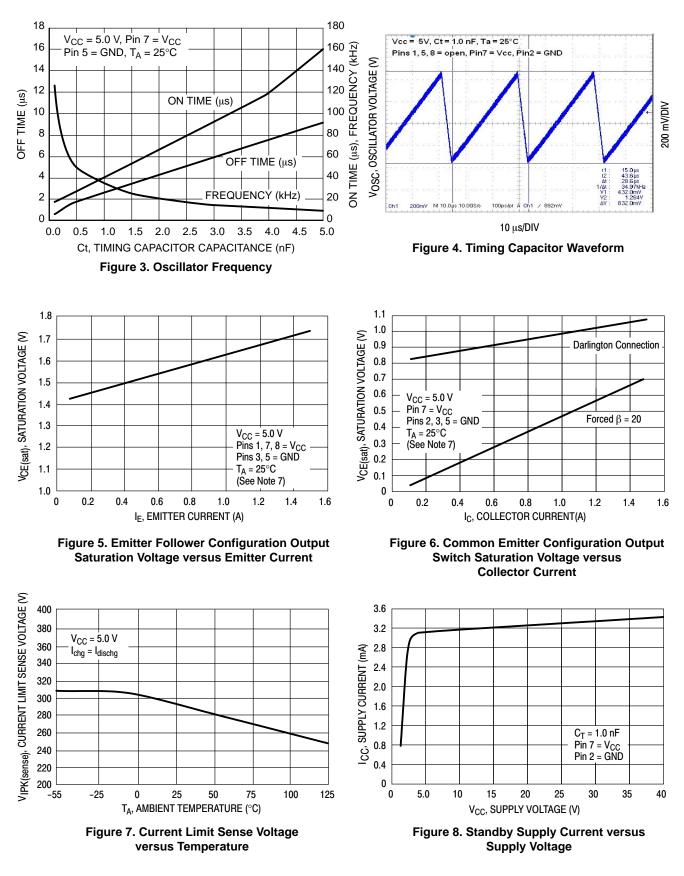
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. $T_{low} = 0^{\circ}C$ for MC34063, SC34063; -40°C for MC33063, SC33063, MC33063V, NCV33063 $T_{high} = +70^{\circ}C$ for MC34063, SC34063; +85°C for MC33063, SC33063; +125°C for MC33063V, NCV33063 5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible. 6. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mÅ) and high driver currents (≥ 30 mÅ), it may take up to 2.0 µs for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is

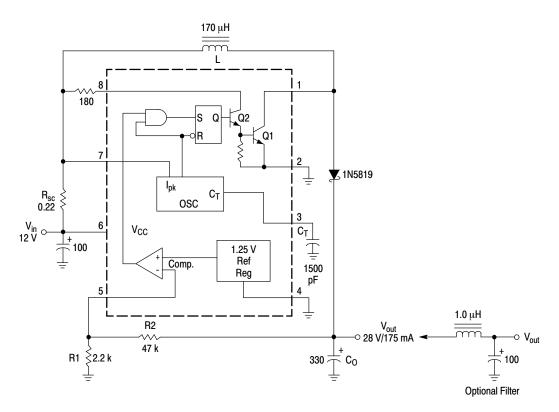
magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

Forced β of output switch : $\frac{IC \text{ output}}{IC \text{ driver} - 7.0 \text{ mA}^*} \ge 10$

* The 100 Ω resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.



7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



Test	Conditions	Results
Line Regulation	V_{in} = 8.0 V to 16 V, I_{O} = 175 mA	30 mV = ±0.05%
Load Regulation	V_{in} = 12 V, I _O = 75 mA to 175 mA	10 mV = ±0.017%
Output Ripple	V _{in} = 12 V, I _O = 175 mA	400 mVpp
Efficiency	V _{in} = 12 V, I _O = 175 mA	87.7%
Output Ripple With Optional Filter	V _{in} = 12 V, I _O = 175 mA	40 mVpp

Figure 9. Step–Up Converter

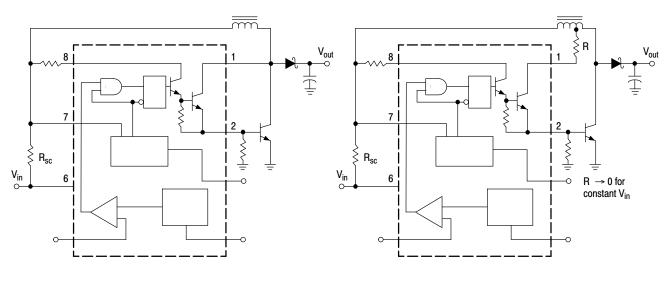
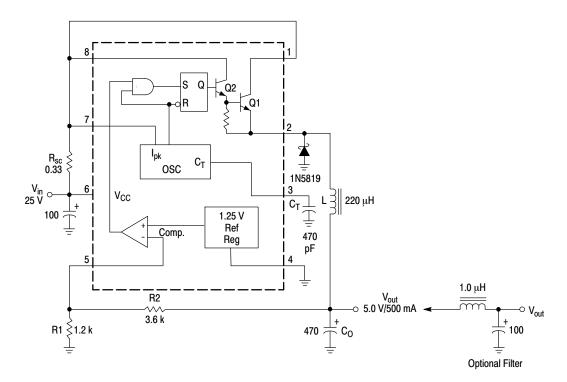


Figure 10. External Current Boost Connections for I_C Peak Greater than 1.5 A

9a. External NPN Switch

9b. External NPN Saturated Switch (See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 µs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.



Test	Conditions	Results
Line Regulation	V_{in} = 15 V to 25 V, I _O = 500 mA	12 mV = ±0.12%
Load Regulation	V_{in} = 25 V, I_O = 50 mA to 500 mA	3.0 mV = ±0.03%
Output Ripple	V _{in} = 25 V, I _O = 500 mA	120 mVpp
Short Circuit Current	V_{in} = 25 V, R_L = 0.1 Ω	1.1 A
Efficiency	V _{in} = 25 V, I _O = 500 mA	83.7%
Output Ripple With Optional Filter	V _{in} = 25 V, I _O = 500 mA	40 mVpp

Figure 11. Step–Down Converter

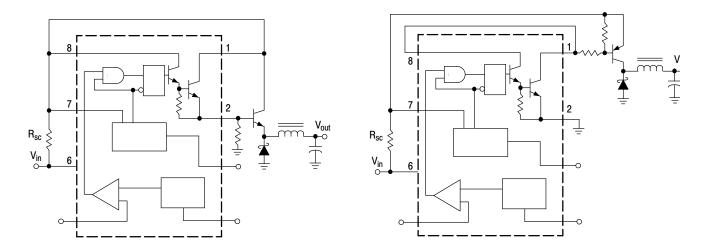
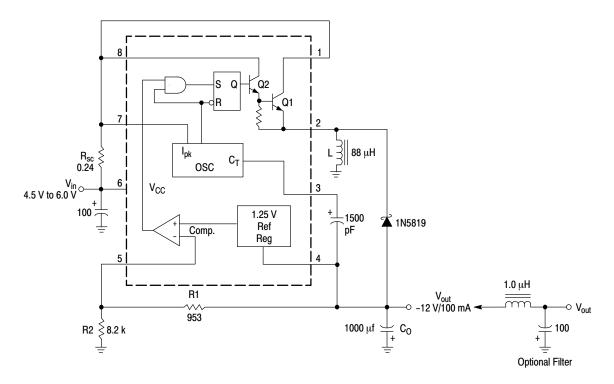


Figure 12. External Current Boost Connections for I_{C} Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch



Test	Conditions	Results
Line Regulation	V_{in} = 4.5 V to 6.0 V, I_{O} = 100 mA	$3.0 \text{ mV} = \pm 0.012\%$
Load Regulation	V_{in} = 5.0 V, I_O = 10 mA to 100 mA	0.022 V = ±0.09%
Output Ripple	$V_{in} = 5.0 \text{ V}, I_0 = 100 \text{ mA}$	500 mVpp
Short Circuit Current	V_{in} = 5.0 V, R_L = 0.1 Ω	910 mA
Efficiency	V _{in} = 5.0 V, I _O = 100 mA	62.2%
Output Ripple With Optional Filter	$V_{in} = 5.0 \text{ V}, I_0 = 100 \text{ mA}$	70 mVpp

Figure 13. Voltage Inverting Converter

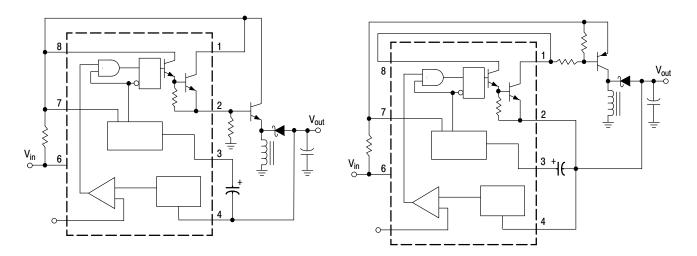
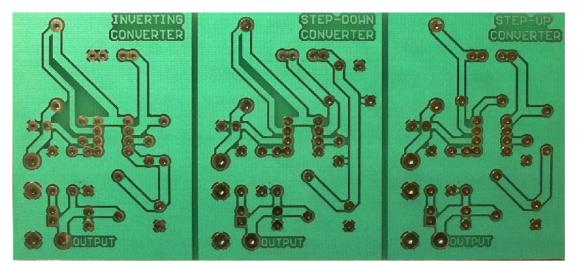
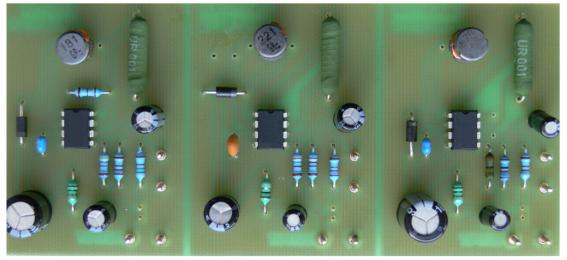


Figure 14. External Current Boost Connections for I_C Peak Greater than 1.5 A13a. External NPN Switch13b. External PNP Saturated Switch



(Bottom Side)



(Top View, Component Side)

Figure 15. Printed Circuit Board and Component Layout (Circuits of Figures 9, 11, 13)

INDUCTOR DATA

Converter	Inductance (μH)	Turns/Wire
Step-Up	170	38 Turns of #22 AWG
Step-Down	220	48 Turns of #22 AWG
Voltage-Inverting	88	28 Turns of #22 AWG

All inductors are wound on Magnetics Inc. 55117 toroidal core.

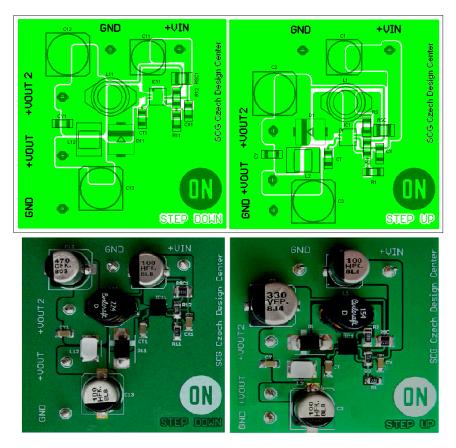


Figure 16. Printed Circuit Board for DFN Device

Calculation	Step–Up	Step-Down	Voltage-Inverting
t _{on} /t _{off}	$\frac{V_{out}\ +\ V_{F}\ -\ V_{in(min)}}{V_{in(min)}\ -\ V_{sat}}$	Vout + V _F V _{in(min)} - V _{sat} - V _{out}	lV _{out} l + V _F V _{in} − V _{sat}
$(t_{on} + t_{off})$	$\frac{1}{f}$	<u>1</u> f	<u>1</u> f
t _{off}	$\frac{\frac{t_{on} + t_{off}}{t_{off}}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{t_{off}}}{\frac{t_{on}}{t_{off}} + 1}$
t _{on}	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$
CT	4.0 x 10 ⁻⁵ t _{on}	4.0 x 10 ⁻⁵ t _{on}	4.0 x 10 ⁻⁵ t _{on}
I _{pk(switch)}	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$	^{2I} out(max)	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$
R _{sc}	0.3/I _{pk(switch)}	0.3/I _{pk(switch)}	0.3/I _{pk(switch)}
L _(min)	$\left(rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}} ight)^t$ on(max)	$\left(\frac{(V_{in(min)} - V_{sat} - V_{out})}{I_{pk(switch)}}\right)t_{on(max)}$	$\left(rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}} ight)^t$ on(max)
C _O	9 <mark>l_{out}t_{on} V_{ripple(pp)}</mark>	$\frac{I_{pk(switch)}(t_{on} + t_{off})}{^{8V}ripple(pp)}$	9 <mark>l_{out}t_{on} V_{ripple(pp)}</mark>

V_{sat} = Saturation voltage of the output switch.

 V_F = Forward voltage drop of the output rectifier.

The following power supply characteristics must be chosen:

V_{in} – Nominal input voltage.

 V_{out} - Desired output voltage, $|V_{out}| = 1.25 \left(1 + \frac{R2}{R1}\right)$

 I_{out} – Desired output current. f_{min} – Minimum desired output switching frequency at the selected values of V_{in} and I_O.

Vripple(pp) – Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

NOTE: For further information refer to Application Note AN920A/D and AN954/D.

Figure 17. Design Formula Table

ORDERING INFORMATION

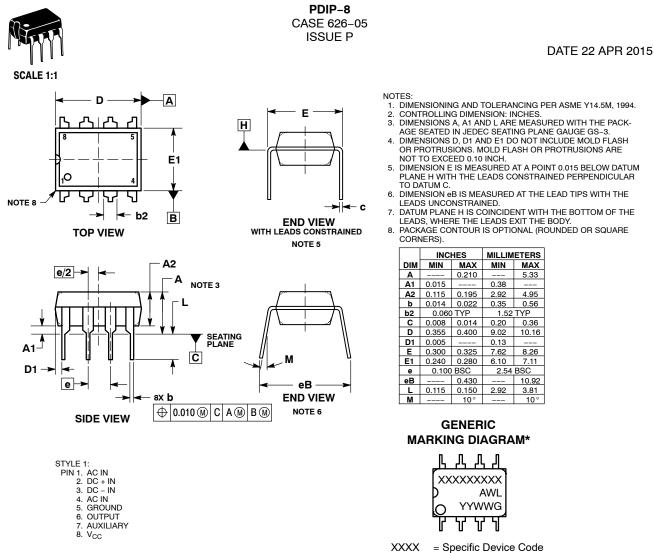
Device	Package	Shipping [†]
MC33063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
SC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail
MC33063AVDG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33063AVDR2G	SOIC-8 (Pb-Free)	
NCV33063AVDR2G*	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC33063AVPG	PDIP-8 (Pb-Free)	50 Units / Rail
MC34063ADG	SOIC-8 (Pb-Free)	98 Units / Rail
MC34063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
MC34063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D. *NCV33063A: $T_{low} = -40^{\circ}$ C, $T_{high} = +125^{\circ}$ C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and

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A = Assembly Location

- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.



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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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